

STARPOWER

SEMICONDUCTOR

IGBT

GD800HFA120C6SD

1200V/800A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as hybrid and electric vehicle.

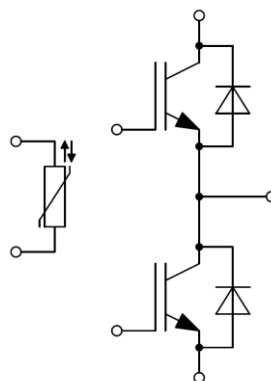
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- Short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Hybrid and electric vehicle
- Inverter for motor drive
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=100^{\circ}\text{C}$	800	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1600	A
P_D	Maximum Power Dissipation @ $T_{vj}=175^{\circ}\text{C}$	4687	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	900	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1800	A
I_{FSM}	Surge Forward Current $t_p=10\text{ms}$ @ $T_{vj}=125^{\circ}\text{C}$ @ $T_{vj}=175^{\circ}\text{C}$	2392	A
		2448	
I^2t	I^2t -value, $t_p=10\text{ms}$ @ $T_{vj}=125^{\circ}\text{C}$ @ $T_{vj}=175^{\circ}\text{C}$	28608	A^2s
		29964	

Module

Symbol	Description	Value	Unit
T_{vjmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{vjop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=800\text{A}, V_{GE}=15\text{V}, T_{vj}=25^\circ\text{C}$		1.40	1.85	V	
		$I_C=800\text{A}, V_{GE}=15\text{V}, T_{vj}=125^\circ\text{C}$		1.60			
		$I_C=800\text{A}, V_{GE}=15\text{V}, T_{vj}=175^\circ\text{C}$		1.60			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=24.0\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^\circ\text{C}$	5.5	6.3	7.0	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_{vj}=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_{vj}=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			0.5		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=100\text{kHz}, V_{GE}=0\text{V}$		28.4		nF	
C_{res}	Reverse Transfer Capacitance				0.15		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		2.05		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=800\text{A}, R_G=0.5\Omega, L_S=40\text{nH}, V_{GE}=-8\text{V}/+15\text{V}, T_{vj}=25^\circ\text{C}$		168		ns	
t_r	Rise Time			78		ns	
$t_{d(off)}$	Turn-Off Delay Time			428		ns	
t_f	Fall Time			123		ns	
E_{on}	Turn-On Switching Loss			43.4		mJ	
E_{off}	Turn-Off Switching Loss			77.0		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=800\text{A}, R_G=0.5\Omega, L_S=40\text{nH}, V_{GE}=-8\text{V}/+15\text{V}, T_{vj}=125^\circ\text{C}$		172		ns
t_r	Rise Time				84		ns
$t_{d(off)}$	Turn-Off Delay Time				502		ns
t_f	Fall Time				206		ns
E_{on}	Turn-On Switching Loss			86.3		mJ	
E_{off}	Turn-Off Switching Loss			99.1		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=800\text{A}, R_G=0.5\Omega, L_S=40\text{nH}, V_{GE}=-8\text{V}/+15\text{V}, T_{vj}=175^\circ\text{C}$			174		ns
t_r	Rise Time				90		ns
$t_{d(off)}$	Turn-Off Delay Time				531		ns
t_f	Fall Time				257		ns
E_{on}	Turn-On Switching Loss			99.8		mJ	
E_{off}	Turn-Off Switching Loss			105		mJ	
I_{SC}	SC Data		$t_p \leq 8\mu\text{s}, V_{GE}=15\text{V}, T_{vj}=150^\circ\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		2600		A
			$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_{vj}=175^\circ\text{C}, V_{CC}=800\text{V}, V_{CEM} \leq 1200\text{V}$		2500		A

Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=900\text{A}, V_{GE}=0\text{V}, T_{vj}=25^\circ\text{C}$		1.60	2.00	V
		$I_F=900\text{A}, V_{GE}=0\text{V}, T_{vj}=125^\circ\text{C}$		1.60		
		$I_F=900\text{A}, V_{GE}=0\text{V}, T_{vj}=175^\circ\text{C}$		1.50		
Q_r	Recovered Charge			47.7		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=800\text{A},$ $-di/dt=7778\text{A}/\mu\text{s}, V_{GE}=-8\text{V},$ $L_S=40\text{nH}, T_{vj}=25^\circ\text{C}$		400		A
E_{rec}	Reverse Recovery Energy			13.6		mJ
Q_r	Recovered Charge			82.7		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=800\text{A},$ $-di/dt=7017\text{A}/\mu\text{s}, V_{GE}=-8\text{V},$ $L_S=40\text{nH}, T_{vj}=125^\circ\text{C}$		401		A
E_{rec}	Reverse Recovery Energy			26.5		mJ
Q_r	Recovered Charge			110		μC
I_{RM}	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=800\text{A},$ $-di/dt=6380\text{A}/\mu\text{s}, V_{GE}=-8\text{V},$ $L_S=40\text{nH}, T_{vj}=175^\circ\text{C}$		413		A
E_{rec}	Reverse Recovery Energy			34.8		mJ

NTC Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		k Ω
$\Delta R/R$	Deviation of R_{100}	$T_c=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$		3433		K

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		20		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.80		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.032	K/W
	Junction-to-Case (per Diode)			0.049	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.030		K/W
	Case-to-Heatsink (per Diode)		0.046		
	Case-to-Heatsink (per Module)		0.009		
M	Terminal Connection Torque, Screw M6	3.0		6.0	N.m
	Mounting Torque, Screw M5	3.0		6.0	
G	Weight of Module		350		g

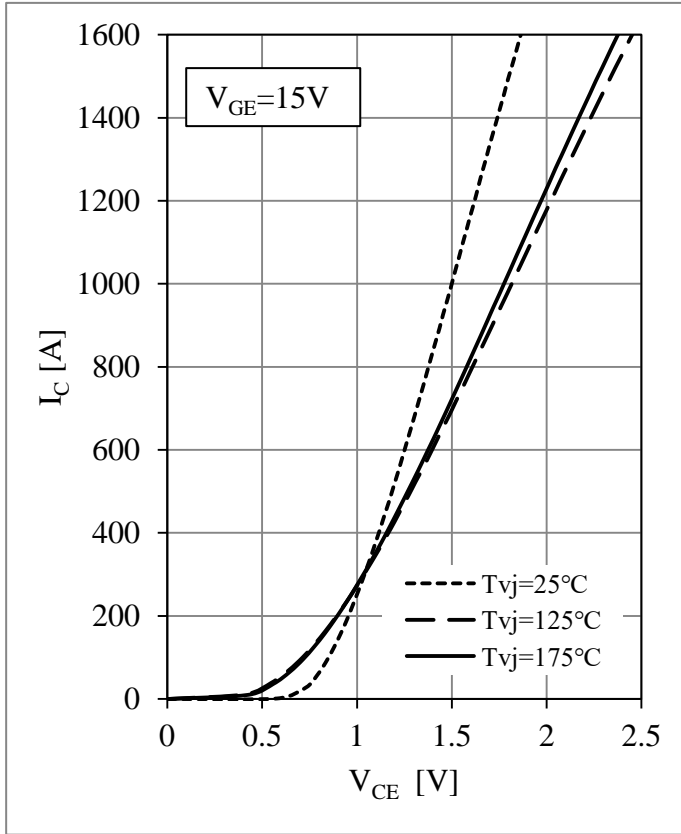


Fig 1. IGBT Output Characteristics

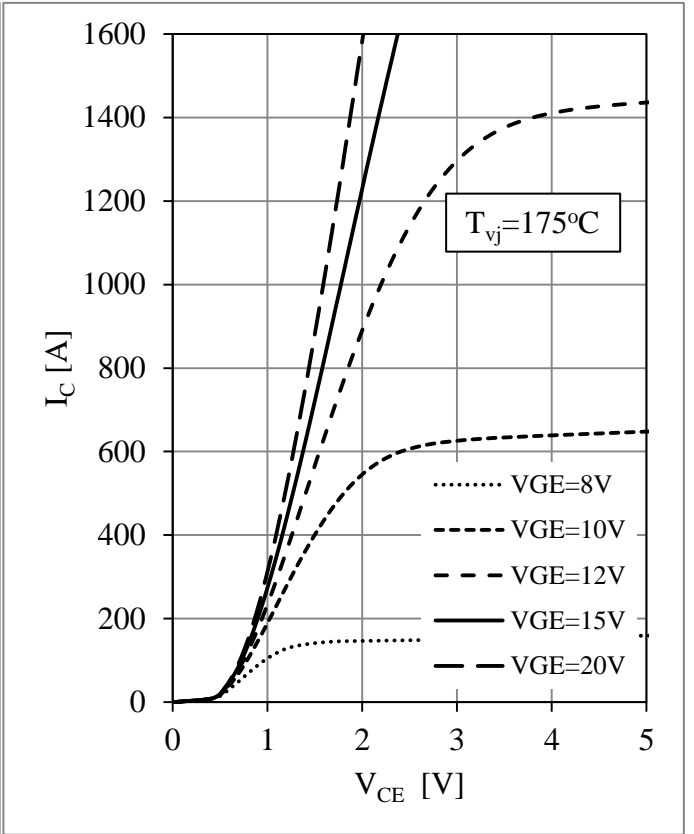


Fig 2. IGBT Transfer Characteristics

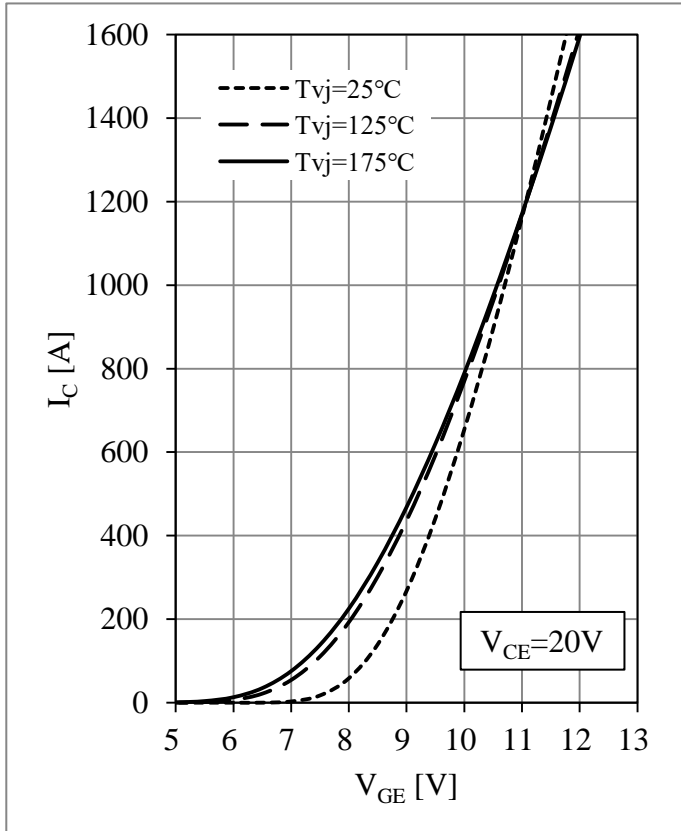


Fig 3. IGBT Transfer Characteristics

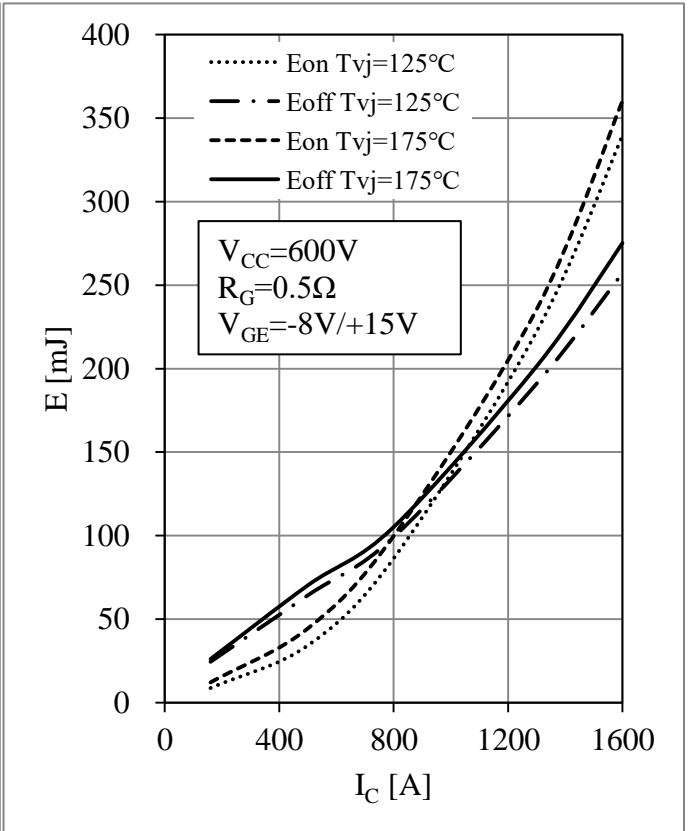


Fig 4. IGBT Switching Loss vs. I_c

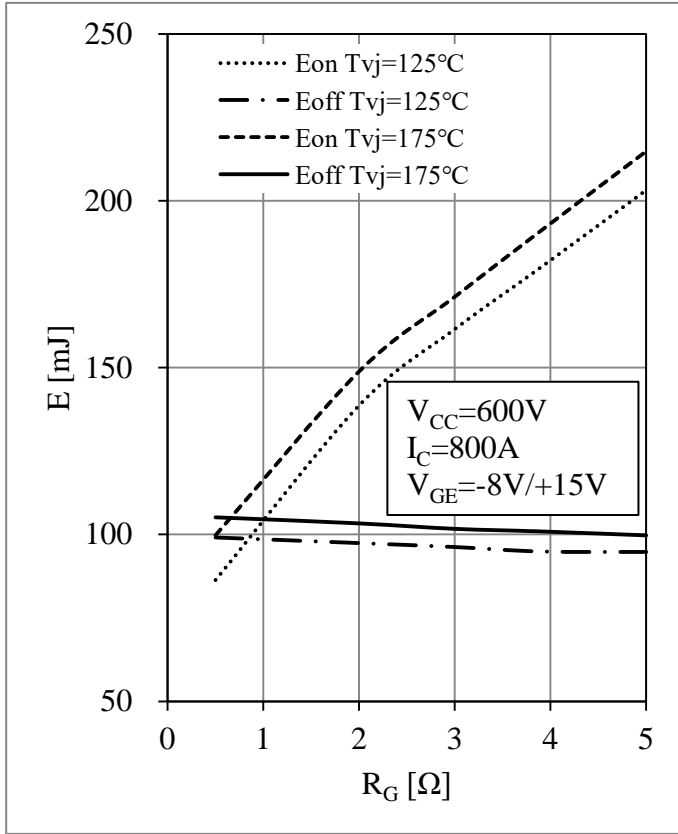


Fig 5. IGBT Switching Loss vs. R_G

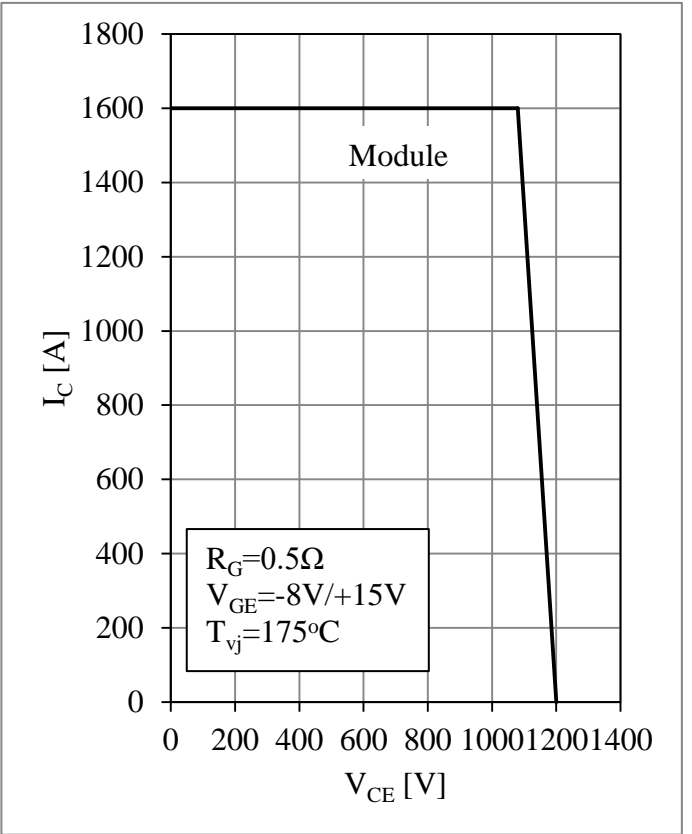


Fig 6. RBSOA

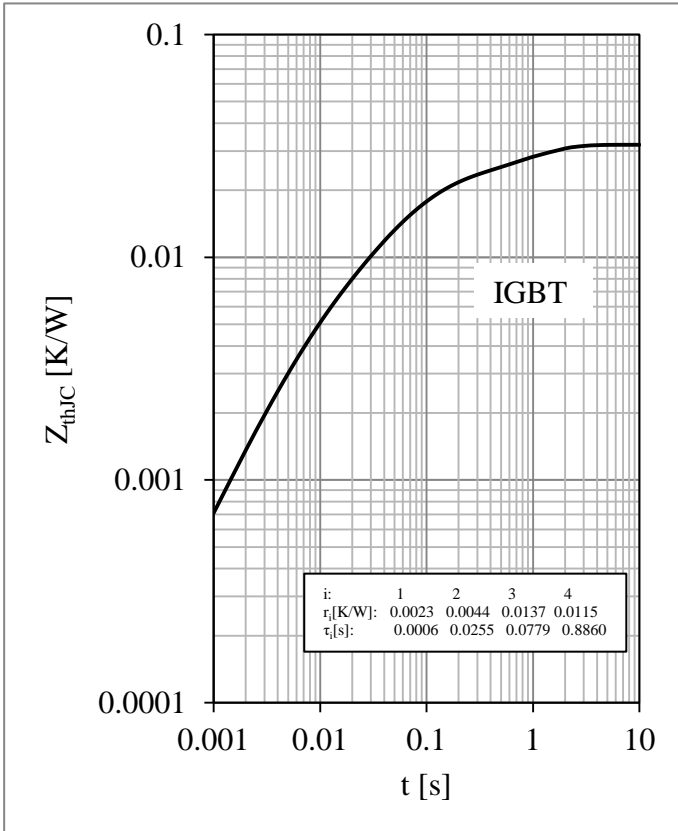


Fig 7. IGBT Transient Thermal Impedance

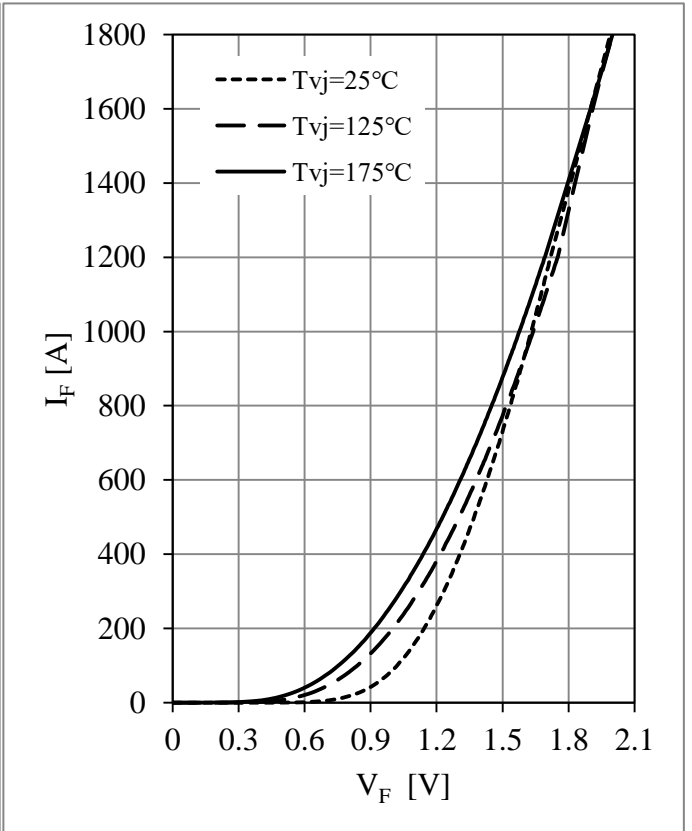


Fig 8. Diode Forward Characteristics

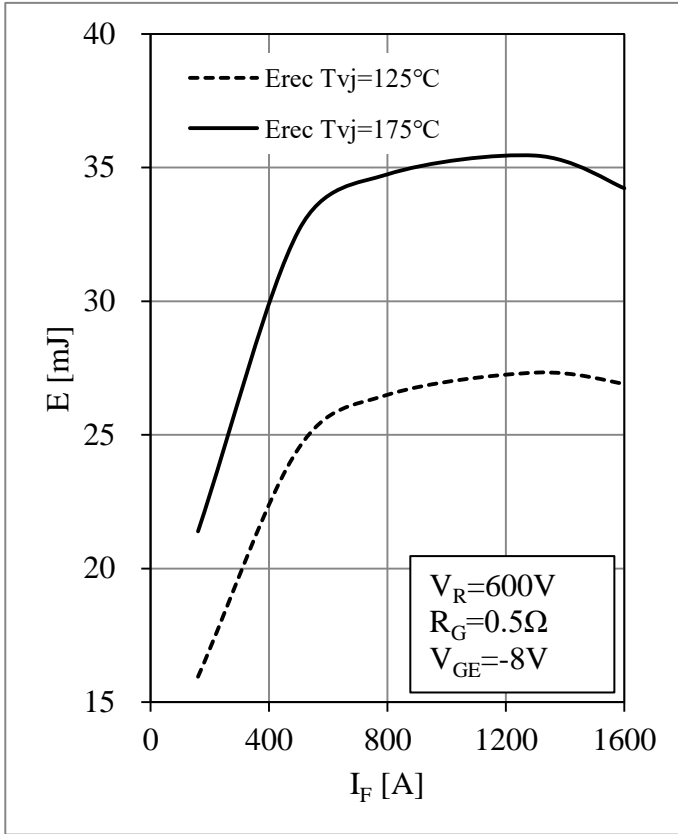


Fig 9. Diode Switching Loss vs. I_F

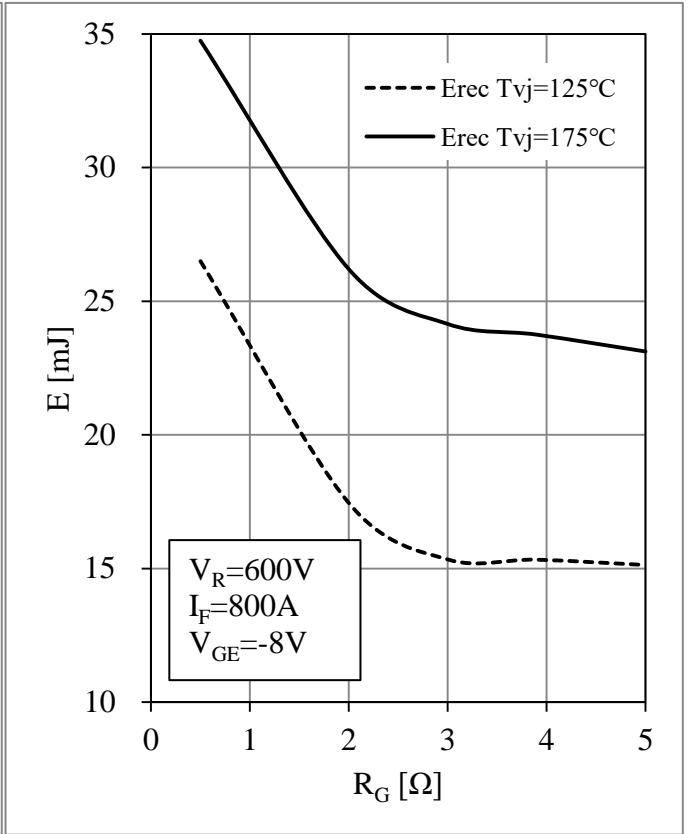


Fig 10. Diode Switching Loss vs. R_G

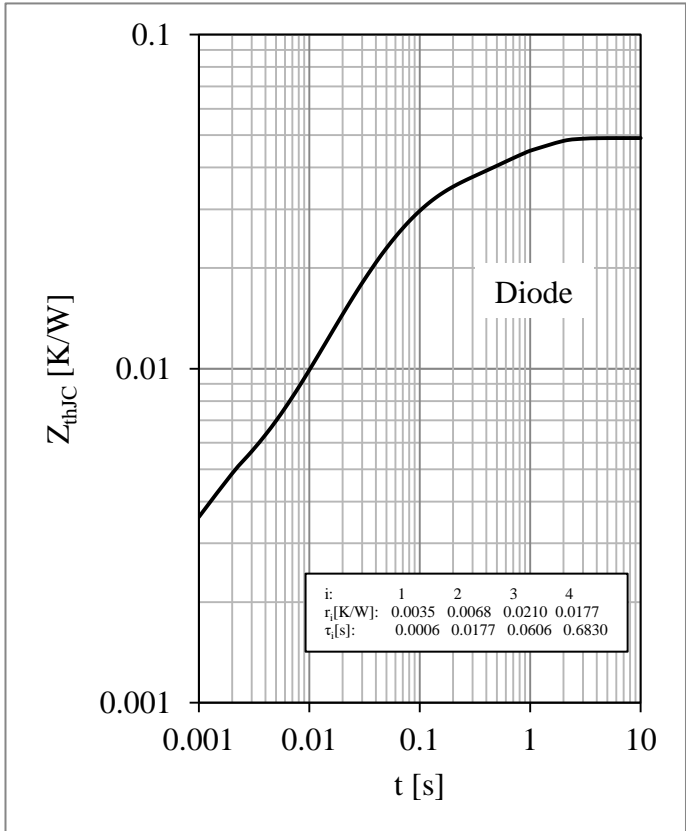


Fig 11. Diode Transient Thermal Impedance

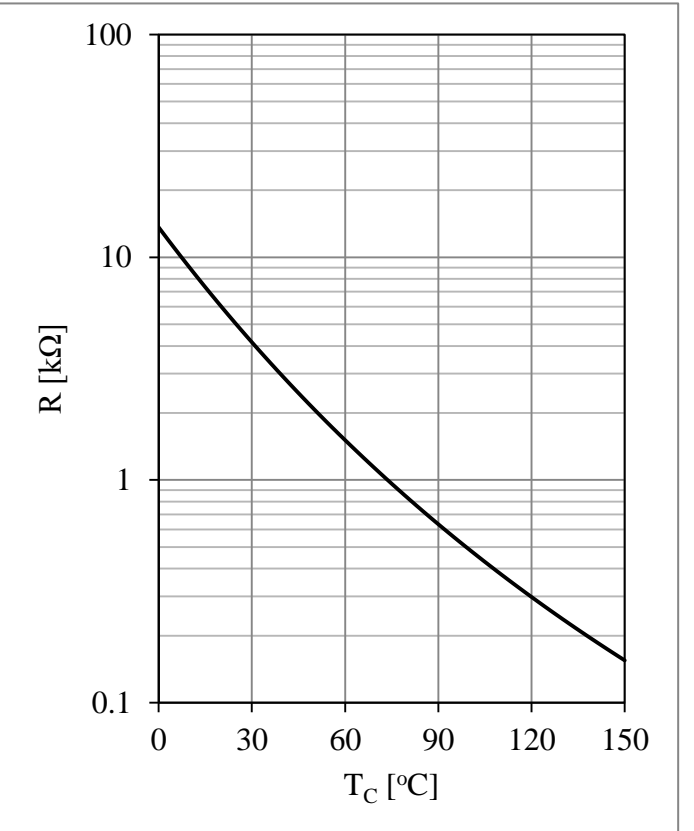
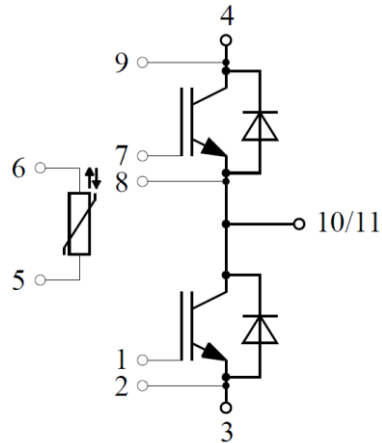


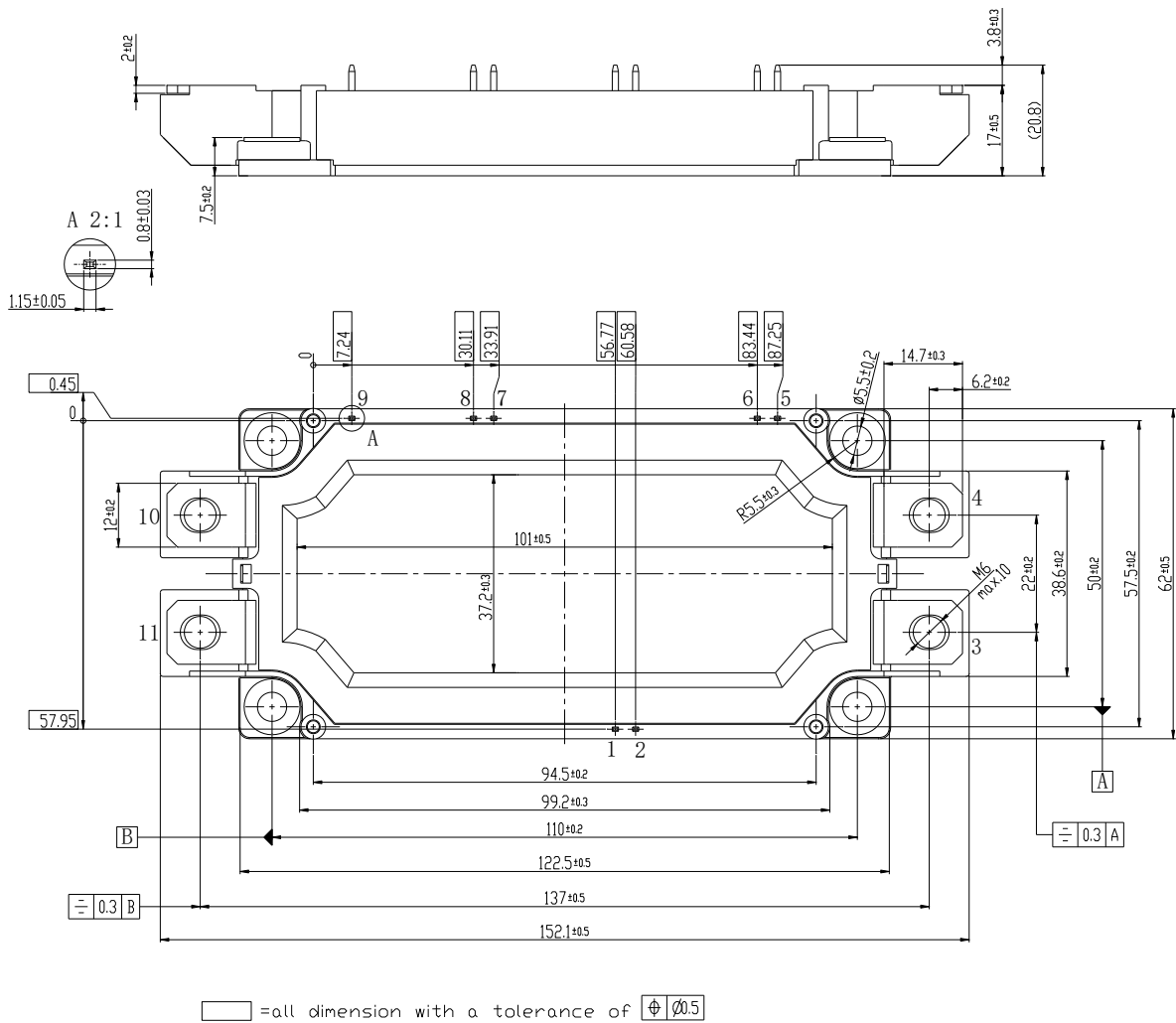
Fig12. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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